



#### **Features**

- Automatic power-down when deselected
- CMOS for optimum speed/power
- High speed ☐ 20 ns
- Low active power □ 660 mW (commercial)
- Low standby power ☐ 110 mW (20 ns)
- TTL-compatible inputs and outputs
- Capable of withstanding greater than 2001V electrostatic discharge
- Available in Pb-free 24-pin Molded SOJ, non Pb-free 24-pin (300-Mil) Molded DIP

## **Functional Description**

The CY7C128A is a high-performance CMOS static RAM organized as 2048 words by 8 bits. Easy memory expansion is provided by an active LOW Chip Enable (CE), and active LOW Output Enable (OE) and tri-state drivers. The CY7C128A has an automatic power-down feature, reducing the power consumption by 83% when deselected.

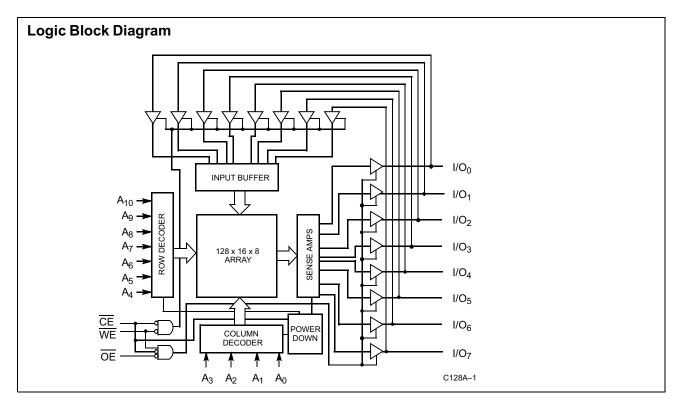
Writing to the device is accomplished when the Chip Enable  $(\overline{CE})$  and Write Enable  $(\overline{WE})$  inputs are both LOW.

Data on the eight I/O pins (I/O<sub>0</sub> through I/O<sub>7</sub>) is written into the memory location specified on the address pins ( $A_0$  through  $A_{10}$ ).

Reading the device is accomplished by taking  $Chip Enable (\overline{CE})$  and  $Output Enable (\overline{OE}) LOW$  while Write Enable  $(\overline{WE})$  remains HIGH. Under these conditions, the contents of the memory location specified on the address pins will appear on the eight I/O pins.

The I/O pins remain in high-impedance state when Chip Enable (CE) or Output Enable (OE) is HIGH or Write Enable (WE) is LOW.

The CY7C128A utilizes a die coat to insure alpha immunity.



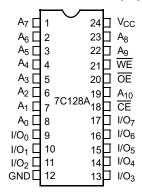


## **Selection Guide**

Description	-20	-45	
Maximum Access Time (ns)	20	45	
Maximum Operating Current (mA)	120	120	
Maximum CMOS Standby Current (mA)	20	20	

# **Pin Configuration**

Figure 1. 24-Pin DIP/SOJ (Top View)





## **Maximum Ratings**

Exceeding the maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature ......-65°C to +150°C

Ambient Temperature with

Power Applied ......55°C to +125°C

Supply Voltage to Ground Potential

(Pin 28 to Pin 14) ......-0.5V to +7.0V

DC Voltage Applied to Outputs

in High Z State ......-0.5V to +7.0V

DC Input Voltage ..... -3.0V to +7.0V

## Output Current into Outputs (LOW)......20 mA Static Discharge Voltage.....>2001V (per MIL-STD-883, Method 3015) Latch-Up Current ...... >200 mA

## **Operating Range**

Range	Ambient Temperature	V <sub>cc</sub>
Commercial	0°C to +70°C	5V ± 10%

## Electrical Characteristics Over the Operating Range<sup>[2]</sup>

Damamastan	Description	Teet Conditions	-2	-20		-45	
Parameter		Test Conditions	Min.	Max.	Min.	Max.	Unit
V <sub>OH</sub>	Output HIGH Voltage	$V_{CC}$ = Min., $I_{OH} = -4.0$ mA	2.4		2.4		V
V <sub>OL</sub>	Output LOW Voltage	$V_{CC}$ = Min., $I_{OL}$ = 8.0 mA		0.4		0.4	V
V <sub>IH</sub>	Input HIGH Voltage		2.2	V <sub>CC</sub>	2.2	V <sub>CC</sub>	V
V <sub>IL</sub>	Input LOW Voltage <sup>[3]</sup>		-0.5	0.8	-0.5	0.8	V
I <sub>IX</sub>	Input Leakage Current	$GND \leq V_I \leq V_CC$	-10	+10	-10	+10	μА
l <sub>oz</sub>	Output Leakage Current	$\begin{aligned} &GND \leq V_I \leq V_{CC} \\ &Output\ Disabled \end{aligned}$	-10	+10	-10	+10	μА
Icc	V <sub>CC</sub> Operating Supply Current	V <sub>CC</sub> = Max. I <sub>OUT</sub> = 0 mA		120		120	mA
I <sub>SB1</sub>	Automatic CE Power-Down Current	$\begin{array}{ll} \text{Max. V}_{\text{CC}}, \overline{\text{CE}} \geq \text{V}_{\text{IH}}, \\ \text{Min. Duty Cycle} = 100\% \end{array} \tag{40}$			20	mA	
I <sub>SB2</sub>	Automatic CE Power-Down Current	$\begin{array}{l} \text{Max. } V_{CC}, \ \overline{CE}_1 \geq V_{CC} - 0.3V, \\ V_{IN} \geq V_{CC} - 0.3V \\ \text{or } V_{IN} \leq 0.3V \end{array}$		20		20	mA

#### Notes:

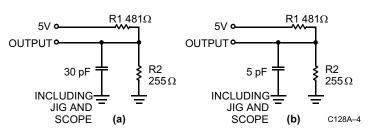
- 1. T<sub>A</sub> is the "instant on" case temperature.
- See the last page of this specification for Group A subgroup testing information.
   V<sub>IL</sub> (min.) = -3.0V for pulse durations less than 30 ns.

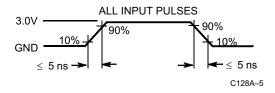


## Capacitance<sup>[4]</sup>

Parameter	Description	Test Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance	$T_A = 25^{\circ}C, f = 1 \text{ MHz},$	10	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>CC</sub> = 5.0V	10	pF

#### **AC Test Loads and Waveforms**





THÉVENIN EQUIVALENT Equivalent to:

## Switching Characteristics Over the Operating Range<sup>[2, 5]</sup>

Damamatan	Decemention		20	-45		
Parameter	Description	Min.	Max.	Min.	Max.	Unit
READ CYCLE		•				
t <sub>RC</sub>	Read Cycle Time	20		45		ns
t <sub>AA</sub>	Address to Data Valid		20		45	ns
t <sub>OHA</sub>	Data Hold from Address Change	5		5		ns
t <sub>ACE</sub>	CE LOW to Data Valid		20		45	ns
t <sub>DOE</sub>	OE LOW to Data Valid		10		20	ns
t <sub>LZOE</sub>	OE LOW to Low Z	3		3		ns
t <sub>HZOE</sub>	OE HIGH to High Z <sup>[6]</sup>		8		15	ns
t <sub>LZCE</sub>	CE LOW to Low Z <sup>[7]</sup>	5		5		ns
t <sub>HZCE</sub> CE HIGH to High Z <sup>[6, 7]</sup>			8		15	ns
t <sub>PU</sub>	CE LOW to Power-Up			0		ns
t <sub>PD</sub>	CE HIGH to Power-Down		20		25	ns
WRITE CYCLE	8)		•	•	'	
t <sub>WC</sub> Write Cycle Time		20		40		ns
t <sub>SCE</sub>	CE LOW to Write End	15		30		ns
t <sub>AW</sub> Address Set-Up to Write End		15		30		ns
t <sub>HA</sub>	Address Hold from Write End	0		0		ns
t <sub>SA</sub>	Address Set-Up to Write Start	0		0		ns
t <sub>PWE</sub>	WE Pulse Width	15 20			ns	
t <sub>SD</sub>	Data Set-Up to Write End	10 15			ns	
t <sub>HD</sub>	Data Hold from Write End	0 0			ns	
t <sub>HZWE</sub>	WE LOW to High Z <sup>[6]</sup>		7		15	ns
t <sub>LZWE</sub>	WE HIGH to Low Z	5		5		ns

#### Notes:

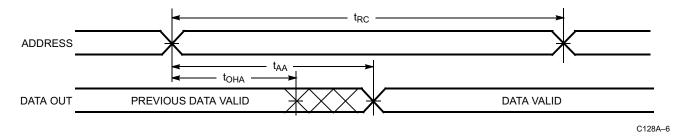
- Tested initially and after any design or process changes that may affect these parameters
   Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified lourloop and the specified lourloop and the specified lourloop.

- 10\_L/10\_H aird 30-pr load capacitarities.
   6. t<sub>HZOE</sub>, t<sub>HZOE</sub>, and t<sub>HZWE</sub> are specified with C<sub>L</sub> = 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady state voltage.
   7. At any given temperature and voltage condition, t<sub>HZOE</sub> is less than t<sub>LZOE</sub> for any given device.
   8. The internal write time of the memory is defined by the overlap of CE LOW and WE LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.

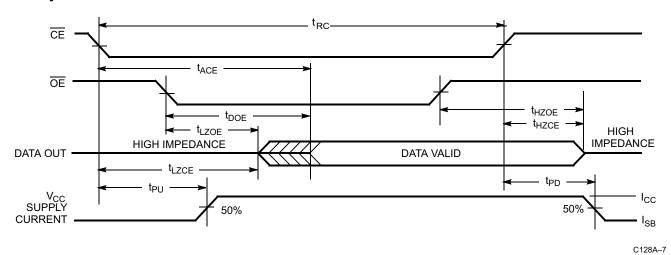


# **Switching Waveforms**

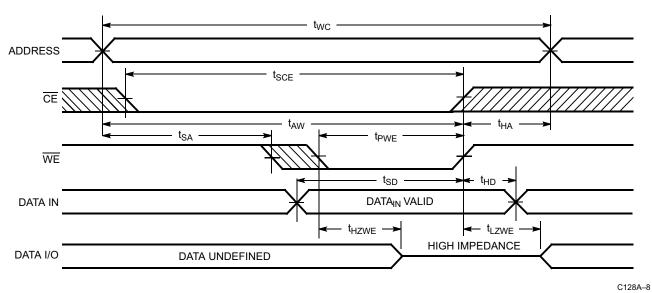
## Read Cycle No. 1<sup>[9, 10]</sup>



# Read Cycle No. 2<sup>[9, 11]</sup>



# Write Cycle No. 1 (WE Controlled)<sup>[8]</sup>



- Notes:

  9. WE is HIGH for read cycle.

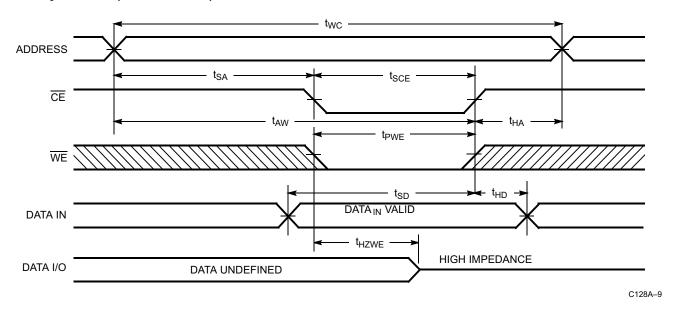
  10. Device is continuously selected. OE, CE = V<sub>IL</sub>.

  11. Address valid prior to or coincident with CE transition LOW.



# Switching Waveforms (continued)

# Write Cycle No. 2 (CE Controlled)[8, 12, 13]

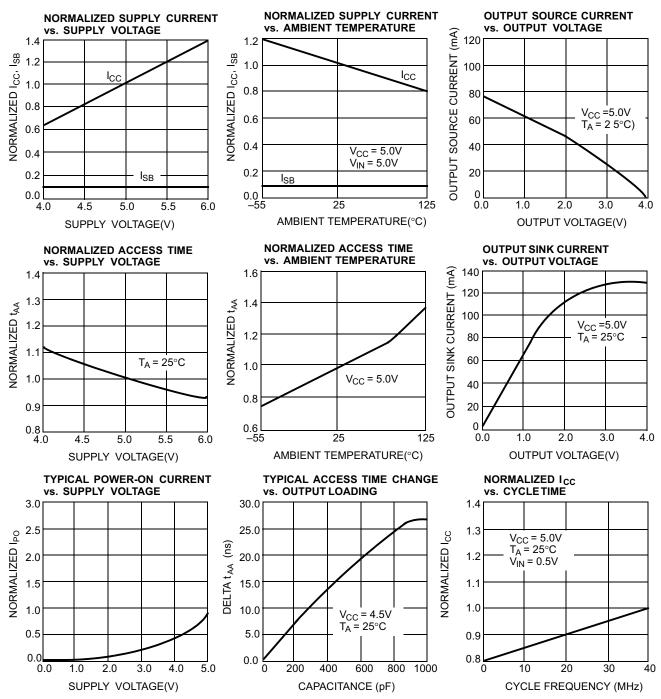


<sup>12.</sup> Data I/O pins enter high-impedance state, as shown, when  $\overline{\text{OE}}$  is held LOW during write.

13. If  $\overline{\text{CE}}$  goes HIGH simultaneously with  $\overline{\text{WE}}$  HIGH, the output remains in a high-impedance state.



# **Typical DC and AC Characteristics**



## **Ordering Information**

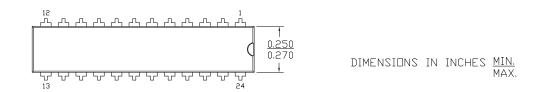
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
20	CY7C128A-20VXC	51-85030	24-pin Molded SOJ (Pb-free)	Commercial
45	CY7C128A-45PC	51-85013	24-pin (300-Mil) Molded DIP	Commercial

Please contact local sales representative regarding availability of these parts



## **Package Diagrams**

Figure 2. 24-pin (300-Mil) Molded DIP (51-85013)



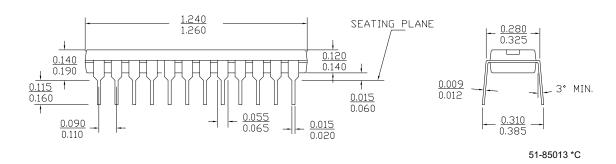
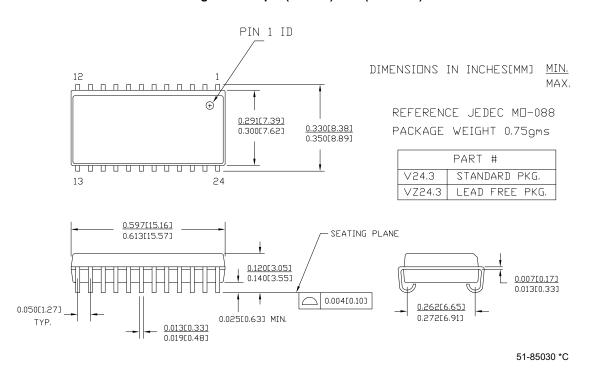


Figure 3. 24-pin (300-Mil) SOJ (51-85030)



Document #: 38-05028 Rev. \*B



### **Document History Page**

Document Title: CY7C128A 2K x 8 Static RAM Document Number: 38-05028					
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change	
**	106814	09/10/01	SZV	Change from Spec number: 38-00094 to 38-05028	
*A	493543	See ECN	NXR	Removed 25 ns speed bin Removed Military Operating Range Changed the description of I <sub>IX</sub> from Input Load Current to Input Leakage Current in DC Electrical Characteristics table Removed I <sub>OS</sub> parameter from DC Electrical Characteristics table Updated ordering Information Table	
*B	2892244	03/19/2010	VKN	Removed 15ns and 35ns speed bin Updated Ordering Information table Updated Package Diagrams (Figure 2 and Figure 3) Added Sales, Solutions, and Legal Information	

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